



FIG. 1A

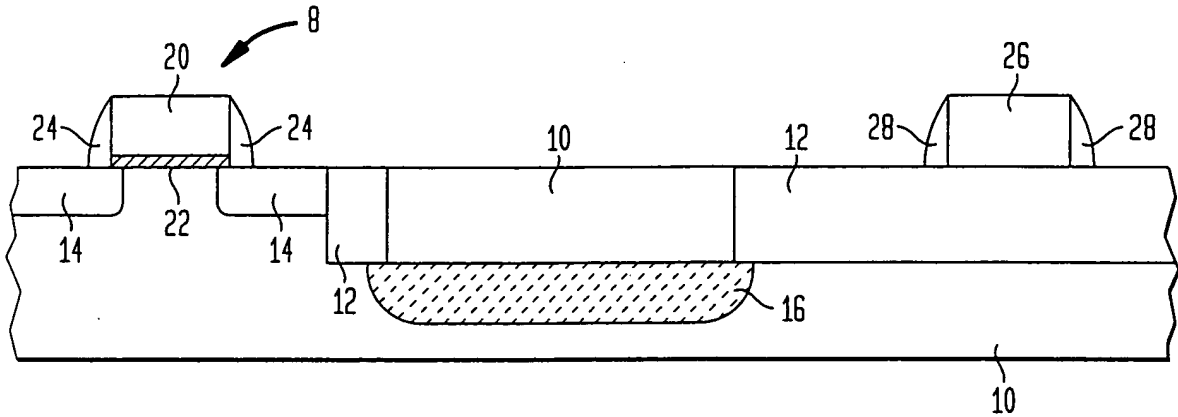


FIG. 1B

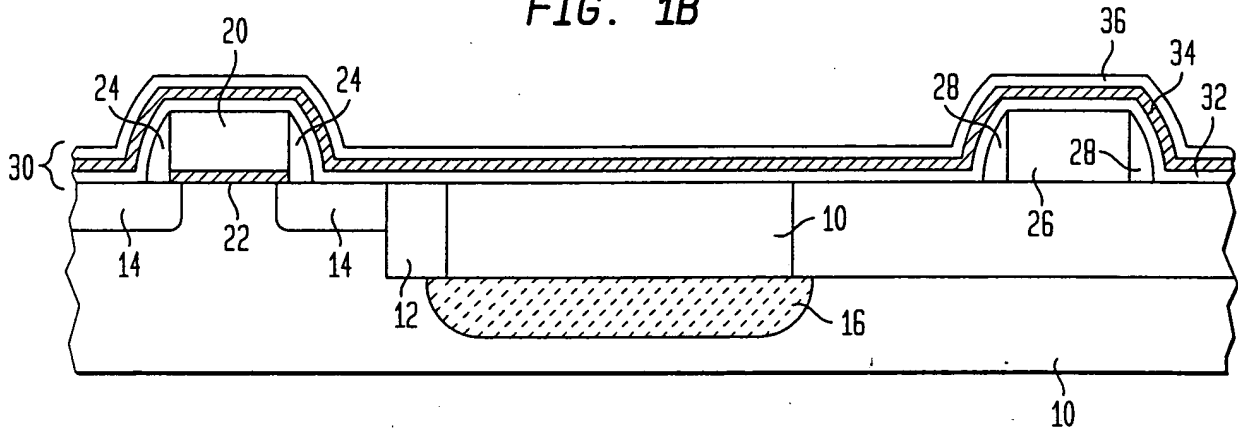
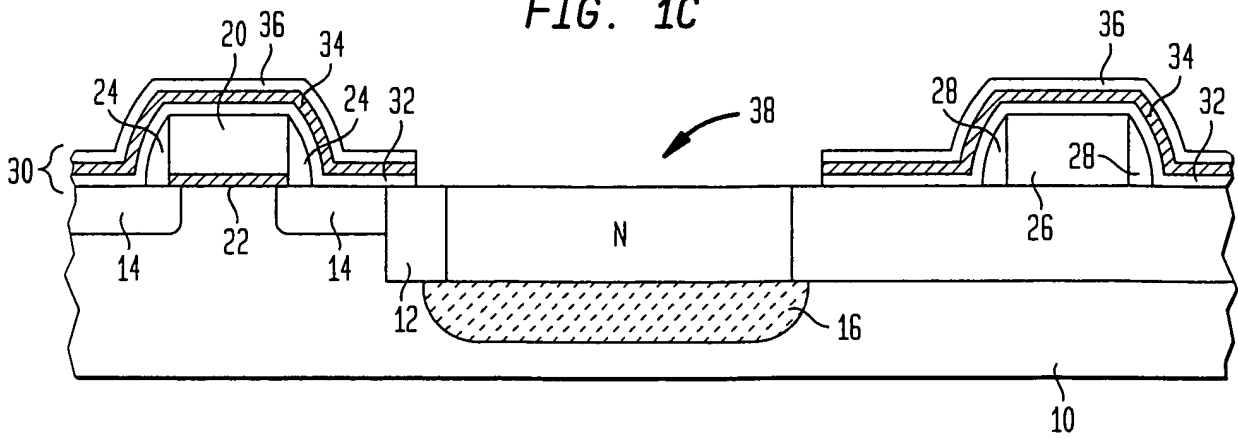
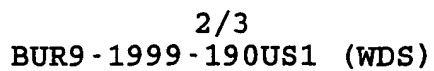


FIG. 1C





This cross-sectional view shows a semiconductor device with a central region labeled 'N' (40) and two side regions, 20 and 26. The device is built on a substrate 10. A layer 12 is present under the central region, and a layer 16 is at the bottom. The side regions 20 and 26 are defined by a layer 22. The top surface of the side regions 20 and 26 is covered by a layer 24, which is further covered by a layer 32. The top surface of the central region 40 is covered by a layer 50, which is further covered by a layer 52. The top surface of the central region 40 is also covered by a layer 28, which is further covered by a layer 34. The top surface of the central region 40 is also covered by a layer 42, which is further covered by a layer 32.

[illegible]

This cross-sectional diagram illustrates a multi-layered semiconductor structure. The base layer is labeled 10. Above it is a layer 26 containing two rectangular regions labeled 28. A central layer is labeled N. Below the N layer is a patterned layer 12 with a semi-circular feature 16. The top surface features several components: a central raised area 52 flanked by hatched regions 50; side structures 42 and 34; and outermost features 24 and 32. Dimensions are indicated at the bottom: 18 for the first section, 48 for the middle section, and 49 for the right section.



FIG. 1G

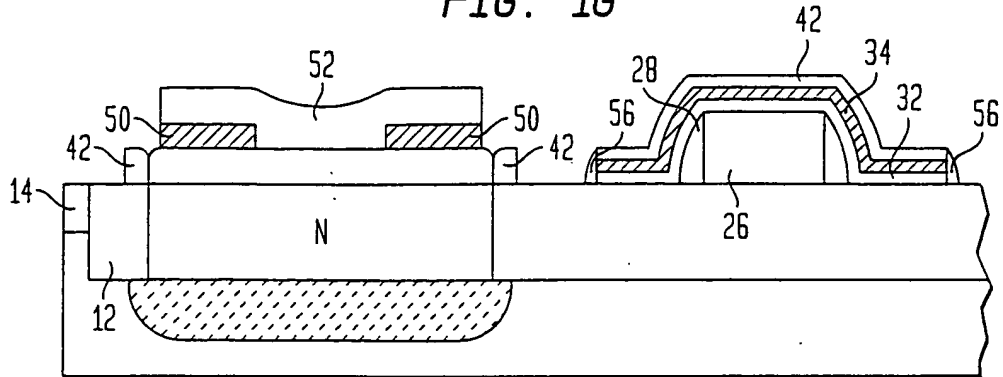


FIG. 2

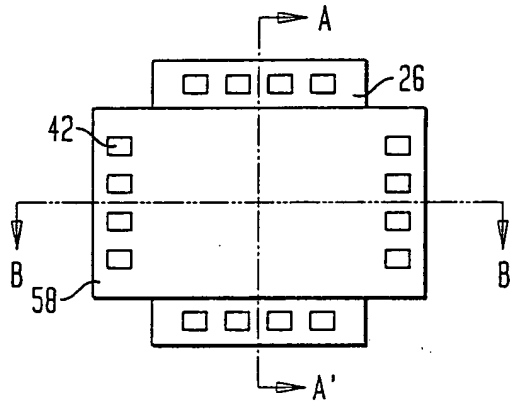


FIG. 3

